

# **isc** Silicon PNP Power Transistors

# MJD32C

## DESCRIPTION

- DC Current Gain -hFE = 25(Min)@ IC= -1A
- Collector-Emitter Breakdown Voltage-: V<sub>(BR) CEO</sub>= -100V(Min)
- Complement to Type MJD31C
- DPAK for Surface Mount Applications
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

### **APPLICATIONS**

• Designed for use in general purpose amplifier and low speed switching applications.

### ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE		UNIT				
V <sub>CBO</sub>	Collector-Base Voltage	-100		V				
V <sub>CEO</sub>	Collector-Emitter Voltage	-100		V				
V <sub>EBO</sub>	Emitter-Base Voltage	-5		V				
Ic	Collector Current-Continuous	-3		А				
I <sub>CM</sub>	Collector Current-Pulse	-5		А				
lΒ	Base Current	-1		А				
Pc	Collector Power Dissipation $T_c$ =25 °C		15	w				
	Collector Power Dissipation $T_a=25^{\circ}C$		1.56					
Tj	Junction Temperature	150		°C				
T <sub>stg</sub>	Storage Ttemperature Range	-65~150		°C				

PARAMETER

Thermal Resistance, Junction to Case

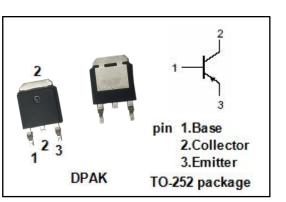
MAX

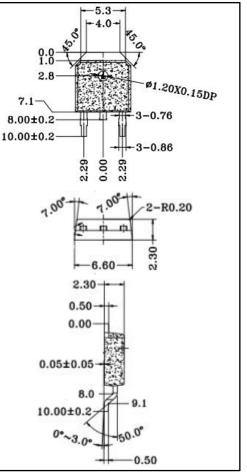
8.3

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UNIT

°C/W





isc Website: www.iscsemi.com

SYMBOL

Rth j-c



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## ELECTRICAL CHARACTERISTICS

#### $T_{\text{c}}\text{=}25^{\circ}\!\!\!\!\!\mathrm{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	МАХ	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = -30mA; I <sub>B</sub> = 0	-100		V
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -3A; I <sub>B</sub> = -0.375A		-1.2	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	I <sub>C</sub> = -3A; V <sub>CE</sub> = -4V		-1.8	V
I <sub>CES</sub>	Collector Cutoff Current	V <sub>CE</sub> = -100V; V <sub>EB</sub> = 0		-20	uA
ICEO	Collector Cutoff Current	V <sub>CE</sub> = -60V; I <sub>B</sub> = 0		-50	uA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = -5V; I <sub>C</sub> = 0		-1.0	mA
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = -1A; V <sub>CE</sub> = -4V	25		
hfe-2	DC Current Gain	I <sub>C</sub> = -3A; V <sub>CE</sub> = -4V	10	50	
fT	Current-Gain—Bandwidth Product	I <sub>C</sub> = -0.5A; V <sub>CE</sub> = -10V	3		MHz

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